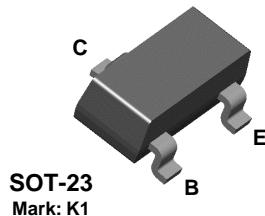


BCW71



NPN General Purpose Amplifier

This device is designed for general purpose amplifier applications at collector currents to 300 mA. Sourced from Process 10.

Absolute Maximum Ratings*

TA = 25°C unless otherwise noted

Symbol	Parameter	Value	Units
V_{CEO}	Collector-Emitter Voltage	45	V
V_{CES}	Collector-Base Voltage	50	V
V_{EBO}	Emitter-Base Voltage	5.0	V
I_C	Collector Current - Continuous	500	mA
T_J, T_{stg}	Operating and Storage Junction Temperature Range	-55 to +150	°C

* These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

NOTES:

- 1) These ratings are based on a maximum junction temperature of 150 degrees C.
- 2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

Thermal Characteristics

TA = 25°C unless otherwise noted

Symbol	Characteristic	Max	Units
		*BCW71	
P_D	Total Device Dissipation Derate above 25°C	350 2.8	mW mW/°C
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	357	°C/W

* Device mounted on FR-4 PCB 40 mm X 40 mm X 1.5 mm.

NPN General Purpose Amplifier

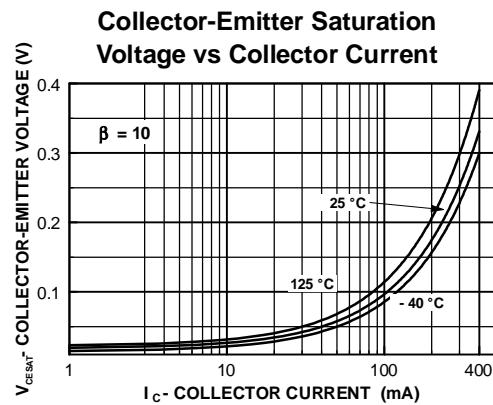
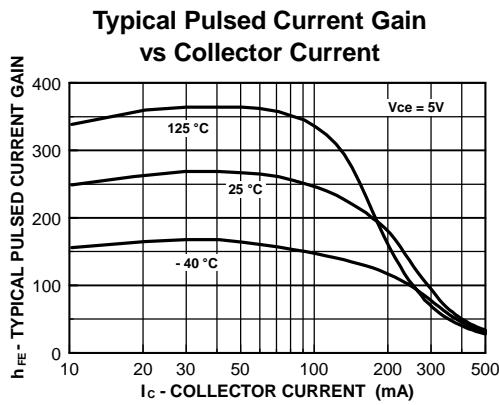
(continued)

Electrical Characteristics

TA = 25°C unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
OFF CHARACTERISTICS						
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	$I_C = 1.0 \text{ mA}$, $I_B = 0$	45			V
$V_{(BR)CBO}$	Collector-Base Breakdown Voltage	$I_C = 10 \mu\text{A}$, $I_E = 0$	50			V
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage	$I_E = 10 \mu\text{A}$, $I_C = 0$	5.0			V
I_{CBO}	Collector-Cutoff Current	$V_{CB} = 20 \text{ V}$, $I_E = 0$ $V_{CB} = 20 \text{ V}$, $I_E = 0$, $T_A = 100^\circ\text{C}$			100 10	μA
ON CHARACTERISTICS						
h_{FE}	DC Current Gain	$I_C = 2.0 \text{ mA}$, $V_{CE} = 5.0 \text{ V}$	110		220	
$V_{CE(\text{sat})}$	Collector-Emitter Saturation Voltage	$I_C = 10 \text{ mA}$, $I_B = 0.5 \text{ mA}$			0.25	V
$V_{BE(\text{sat})}$	Base-Emitter Saturation Voltage	$I_C = 50 \text{ mA}$, $I_B = 2.5 \text{ mA}$		0.85		V
$V_{BE(\text{on})}$	Base-Emitter On Voltage	$I_C = 2.0 \text{ mA}$, $V_{CE} = 5.0 \text{ V}$	0.6		0.75	V
SMALL SIGNAL CHARACTERISTICS						
f_T	Current Gain - Bandwidth Product	$I_C = 10 \text{ mA}$, $V_{CE} = 5.0 \text{ V}$, $f = 35 \text{ MHz}$		330		MHz
C_{obo}	Output Capacitance	$V_{CE} = 10 \text{ V}$, $I_E = 0$, $f = 1.0 \text{ MHz}$			4.0	pF
C_{ibo}	Input Capacitance	$V_{EB} = 0.5 \text{ V}$, $I_C = 0$, $f = 1.0 \text{ MHz}$		9.0		pF
NF	Noise Figure	$I_C = 0.2 \text{ mA}$, $V_{CE} = 5.0 \text{ V}$, $R_S = 2.0 \text{ k}\Omega$, $f = 1.0 \text{ kHz}$, $BW = 200 \text{ Hz}$			10	dB

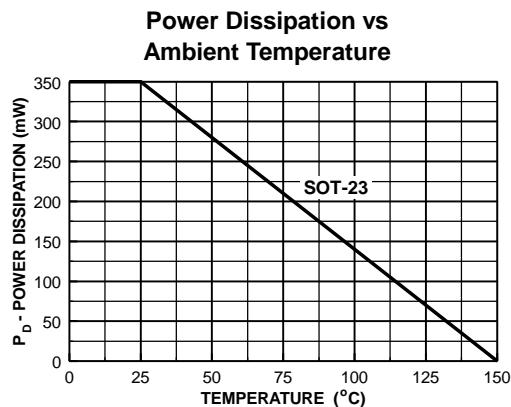
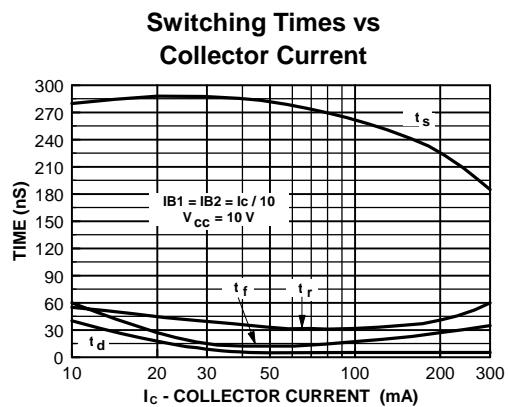
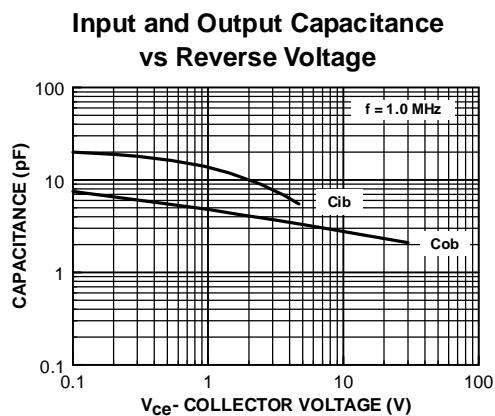
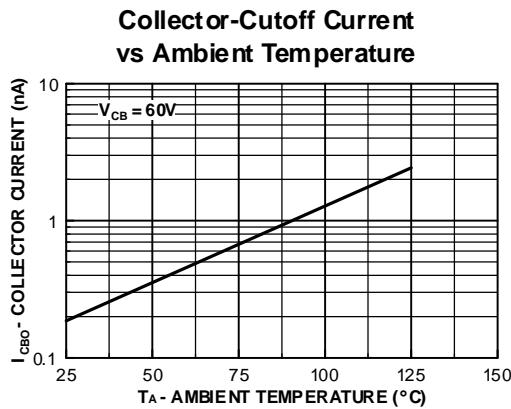
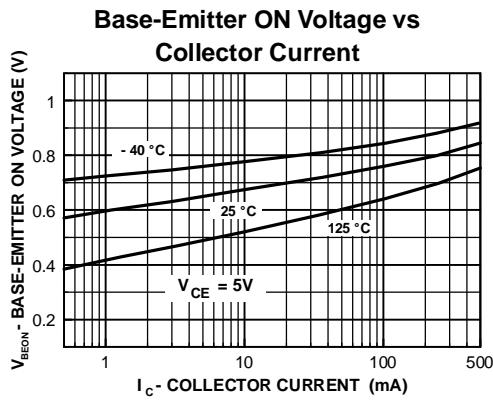
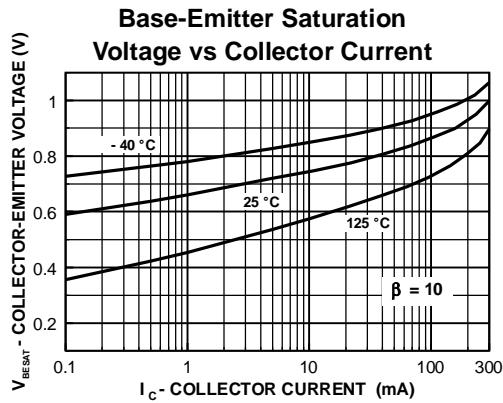
Typical Characteristics



NPN General Purpose Amplifier

(continued)

Typical Characteristics (continued)



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